











CSD95372BQ5M

SLPS499B - MARCH 2014-REVISED MARCH 2016

CSD95372BQ5M Synchronous Buck NexFET™ Smart Power Stage

Features

- 60 A Continuous Operating Current Capability
- 93.4% System Efficiency at 30 A
- Low Power Loss of 2.8 W at 30 A
- High-Frequency Operation (up to 1.25 MHz)
- Diode Emulation Mode With FCCM
- Temperature Compensated Bi-Directional Current Sense
- Analog Temperature Output (600 mV at 0°C)
- **Fault Monitoring**
 - High-Side Short, Overcurrent, and Overtemperature Protection
- 3.3 and 5-V PWM Signal Compatible
- Tri-State PWM Input
- Integrated Bootstrap Diode
- Optimized Deadtime for Shoot Through Protection
- High-Density SON 5 × 6 mm Footprint
- Ultra-Low Inductance Package
- System Optimized PCB Footprint
- RoHS Compliant Lead-Free Terminal Plating
- Halogen Free

2 Applications

- Multiphase Synchronous Buck Converters
 - **High-Frequency Applications**
 - High-Current, Low-Duty Cycle Applications
- POL DC-DC Converters
- Memory and Graphic Cards
- Desktop and Server VR11.x / VR12.x V-Core and Memory Synchronous Converters

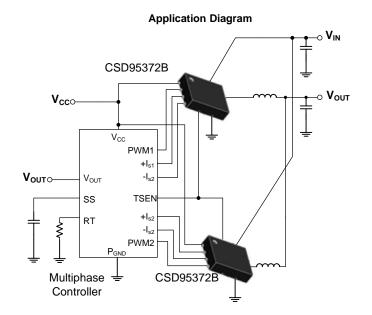
3 Description

The CSD95372BQ5M NexFET™ smart power stage is a highly optimized design for use in a high-power, high-density Synchronous Buck converter. This product integrates the Driver IC and Power MOSFETs to complete the power stage switching function. This combination produces high-current, high-efficiency, and high-speed switching capability in a small 5-mm x 6-mm outline package. It also integrates the accurate current sensing temperature sensing functionality to simplify system design and improve accuracy. In addition, the PCB footprint has been optimized to help reduce design time and simplify the completion of the overall system design.

Device Information(1)

Device	Media	Qty	Package	Ship
CSD95372BQ5M	13-Inch Reel	2500	SON	Tape
CSD95372BQ5MT	7-Inch Reel	250	5 mm × 6 mm Package	and Reel

(1) For all available packages, see the orderable addendum at the end of the data sheet.



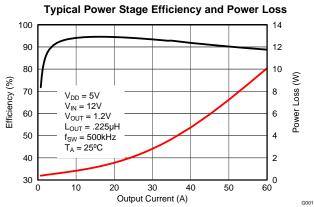




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4 Revision History

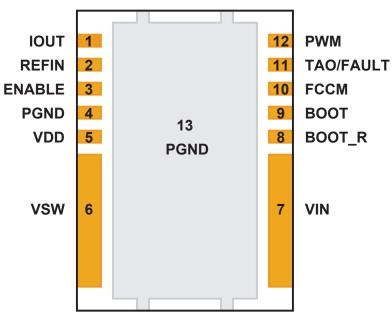
Changes from Revision A (June 2014) to Revision B Changed application schematic to show I _{OUT} (not I _{MON}) for each CSD95372B device. Changes from Original (March 2014) to Revision A Removed "input voltage up to 14.5 V" and "DualCool™ package" bullets from the Features. Fixed TAO/FAULT pin function to state that TAO will be pulled up to 3.3 V in the event of thermal shutdown	Page
Changed application schematic to show I _{OUT} (not I _{MON}) for each CSD95372B device	5
Changes from Original (March 2014) to Revision A	Page
 Removed "input voltage up to 14.5 V" and "DualCool™ package" bullets from the Features 	1
• Fixed TAO/FAULT pin function to state that TAO will be pulled up to 3.3 V in the event of thermal shutdown .	3
Added minimum ESD Ratings	4
Increased maximum input voltage to 16 V	<u>∠</u>
Added table note for max input voltage	

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5 Pin Configuration and Functions





Pin Functions

		Pin Functions
P	IN	DESCRIPTION
NAME	NUMBER	DESCRIPTION
воот	9	Bootstrap capacitor connection. Connect a minimum of 0.1 μ F 16 V X7R ceramic capacitor from BOOT to BOOT_R pins. The bootstrap capacitor provides the charge to turn on the control FET. The bootstrap diode is integrated.
BOOT_R	8	Return path for HS gate driver, connected to V _{SW} internally.
ENABLE	3	Enables device operation. If ENABLE = logic HIGH, turns on device. If ENABLE = logic LOW, the device is turned off and both MOSFET gates are actively pulled low. An internal 100-k Ω pulldown resistor will pull the ENABLE pin LOW if left floating.
FCCM	10	This pin enables the Diode Emulation function. When this pin is held LOW, Diode Emulation Mode is enabled for sync FET. When FCCM is HIGH, the device is operated in Forced Continuous Conduction Mode. An internal 5 μ A current source will pull the FCCM pin to 3.3 V if left floating.
IOUT	1	Output of current sensing amplifier. V(IOUT) – V(REFIN) is proportional to the phase current.
P_{GND}	4	Power ground, connected directly to pin 13.
P_{GND}	13	Power ground
PWM	12	Pulse width modulated 3-state input from external controller. Logic LOW sets control FET gate low and sync FET gate high. Logic HIGH sets control FET gate high and sync FET gate low. Open or High Z sets both MOSFET gates low if greater than the 3-state shutdown hold-off time (t _{3HT}).
REFIN	2	External reference voltage input for current sensing amplifier
TAO/ FAULT	11	Temperature Analog Output. Reports a voltage proportional to the die temperature. An ORing diode is integrated in the IC. When used in multiphase application, a single wire can be used to connect the TAO pins of all the IC's. Only the highest temperature will be reported. TAO will be pulled up to 3.3 V if thermal shutdown occurs. TAO should be bypassed to P _{GND} with a 1-nF 16-V X7R ceramic capacitor.
V_{DD}	5	Supply voltage to gate driver and internal circuitry
V_{IN}	7	Input voltage pin. Connect input capacitors close to this pin.
V_{SW}	6	Phase node connecting the HS MOSFET source and LS MOSFET drain – pin connection to the output inductor.

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6 Specifications

6.1 Absolute Maximum Ratings

 $T_{\Delta} = 25^{\circ}C$ (unless otherwise noted)⁽¹⁾

	MIN	MAX	UNIT
V _{IN} to P _{GND}	-0.3	25	V
V _{IN} to V _{SW}	-0.3	25	V
V _{IN} to V _{SW} (10 ns)	-7	27	V
V _{SW} to P _{GND}	-0.3	20	V
V _{SW} to P _{GND} (10 ns)	-7	23	V
V _{DD} to P _{GND}	-0.3	7	V
ENABLE, PWM, FCCM. TAO, IOUT, REFIN to P _{GND}	-0.3	$V_{DD} + 0.3 V$	V
BOOT to BOOT_R ⁽²⁾	-0.3	$V_{DD} + 0.3 V$	V
P _D , power dissipation		12	W
T _J , operating junction	-55	150	°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 Handling Ratings

			MIN	MAX	UNIT
T _{stg}	Storage temperature range)	- 55	150	°C
V	Electrostatic discharge	Human body model (HBM)	-2000	2000	V
V _(ESD)		Charged device model (CDM)	-500	500	V

6.3 Recommended Operating Conditions

T_A = 25° (unless otherwise noted)

			MIN	MAX	UNIT
V_{DD}	Gate drive voltage		4.5	5.5	V
V _{IN}	Input supply voltage (1)			16	V
V_{OUT}	Output voltage			5.5	V
I _{OUT}	Continuous output current	$V_{IN} = 12 \text{ V}, V_{DD} = 5 \text{ V}, V_{OUT} = 1.2 \text{ V},$ $f_{SW} = 500 \text{ kHz}, L_{OUT} = 0.225 \mu H^{(2)}$		60	
I _{OUT-PK}	Peak output current ⁽³⁾	$f_{SW} = 500 \text{ kHz}, L_{OUT} = 0.225 \mu H^{(2)}$		90	Α
$f_{\sf SW}$	Switching frequency	$C_{BST} = 0.1 \mu F (min)$		1250	kHz
	On-time duty cycle	$f_{SW} = 1 \text{ MHz}$		85	%
	Minimum PWM on-time		40		ns
	Operating temperature		-40	125	°C

⁽¹⁾ Operating at high V_{IN} can create excessive AC voltage overshoots on the switch node (V_{SW}) during MOSFET switching transients. For reliable operation, the switch node (V_{SW}) to ground voltage must remain at or below the Absolute Maximum Ratings.

6.4 Thermal Information

 $T_A = 25^{\circ}C$ (unless otherwise noted)

	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{ heta JC}$	Junction-to-case thermal resistance (top of package) ⁽¹⁾			15	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance ⁽²⁾			1.5	°C/W

⁽¹⁾ R_{0JC} is determined with the device mounted on a 1 inch² (6.45 cm²), 2 oz (0.071 mm thick) Cu pad on a 1.5 inches x 1.5 inches, 0.06 inch (1.52 mm) thick FR4 board.

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⁽²⁾ Should not exceed 7 V

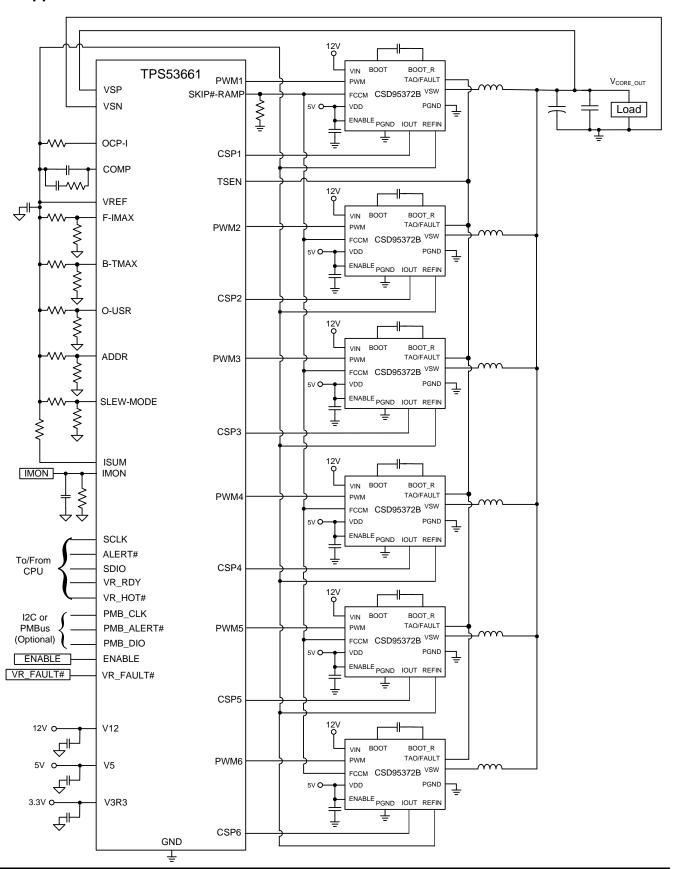
⁽²⁾ Measurement made with six 10 µF (TDK C3216X5R1C106KT or equivalent) ceramic capacitors placed across V_{IN} to P_{GND} pins.

⁽³⁾ System conditions as defined in Note 1. Peak output current is applied for $t_p = 50 \mu s$.

⁽²⁾ $R_{\theta JB}$ value based on hottest board temperature within 1 mm of the package.



7 Application Schematic





8 Device and Documentation Support

8.1 Trademarks

NexFET, DualCool are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

8.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

8.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

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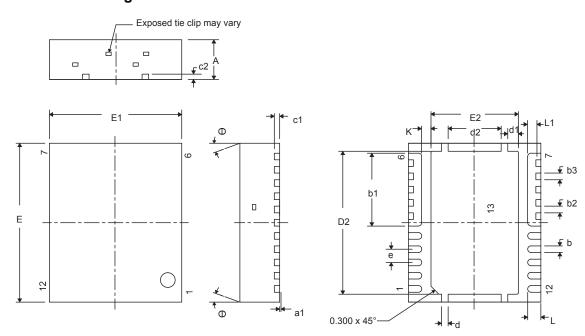
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9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

9.1 Mechanical Drawing



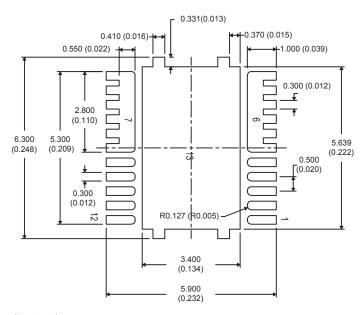
DIM		MILLIMETERS		INCHES				
DIM	MIN	NOM	MAX	MIN	NOM	MAX		
Α	1.400	1.450	1.500	0.057	0.059	0.061		
a1	0.000	0.000	0.050	0.000	0.000	0.002		
b	0.200	0.250	0.320	0.008	0.010	0.013		
b1		2.750 TYP			0.108 TYP			
b2	0.200	0.250	0.320	0.008	0.010	0.013		
b3		0.250 TYP			0.010 TYP			
c1	0.150		0.250	0.006	0.006 0.008			
c2	0.200	0.250	0.300	0.008	0.010	0.012		
D2	5.300	5.400	5.500	0.209	0.213	0.217		
d	0.200	0.250	0.300	0.008	0.010	0.012		
d1	0.350	0.400	0.450	0.014	0.016	0.018		
d2	1.900	2.000	2.100	0.075	0.079	0.083		
E	5.900	6.000	6.100	0.232	0.236	0.240		
E1	4.900	5.000	5.100	0.193	0.197	0.201		
E2	3.200	3.300	3.400	0.126	0.130	0.134		
е		0.500 TYP			0.020 TYP			
K	0.350 TYP				0.014 TYP			
L	0.400	0.500	0.600	0.016	0.020	0.024		
L1	0.210	0.310	0.410	0.008	0.012	0.016		
θ	0.00	_	_	0.00	_	_		

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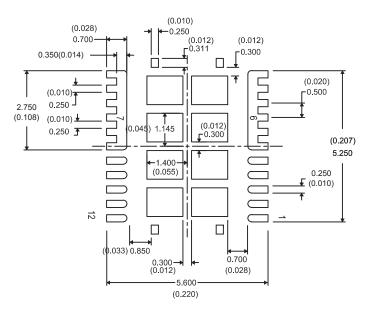


9.2 Recommended PCB Land Pattern



1. Dimensions are in mm (inches).

9.3 Recommended Stencil Opening



- 1. Dimensions are in mm (inches).
- 2. Stencil thickness is 100 μm.

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/			Part marking
	(1)	(2)			(3)	Ball material Peak reflow			(6)
						(4)	(5)		
CSD95372BQ5M	Active	Production	LSON-CLIP (DQP) 12	2500 LARGE T&R	ROHS Exempt	NIPDAU	Level-2-260C-1 YEAR	-55 to 150	95372BM
CSD95372BQ5M.A	Active	Production	LSON-CLIP (DQP) 12	2500 LARGE T&R	ROHS Exempt	NIPDAU	Level-2-260C-1 YEAR	-55 to 150	95372BM
CSD95372BQ5M.B	Active	Production	LSON-CLIP (DQP) 12	2500 LARGE T&R	-	Call TI	Call TI	-55 to 150	
CSD95372BQ5MG4	Active	Production	LSON-CLIP (DQP) 12	2500 LARGE T&R	ROHS Exempt	NIPDAU	Level-2-260C-1 YEAR	-55 to 150	95372BM
CSD95372BQ5MG4.A	Active	Production	LSON-CLIP (DQP) 12	2500 LARGE T&R	ROHS Exempt	NIPDAU	Level-2-260C-1 YEAR	-55 to 150	95372BM
CSD95372BQ5MG4.B	Active	Production	LSON-CLIP (DQP) 12	2500 LARGE T&R	-	Call TI	Call TI	-55 to 150	
CSD95372BQ5MT	Active	Production	LSON-CLIP (DQP) 12	250 SMALL T&R	ROHS Exempt	NIPDAU SN	Level-2-260C-1 YEAR	-55 to 150	95372BM
CSD95372BQ5MT.A	Active	Production	LSON-CLIP (DQP) 12	250 SMALL T&R	ROHS Exempt	NIPDAU	Level-2-260C-1 YEAR	-55 to 150	95372BM
CSD95372BQ5MT.B	Active	Production	LSON-CLIP (DQP) 12	250 SMALL T&R	-	Call TI	Call TI	-55 to 150	

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PACKAGE OPTION ADDENDUM

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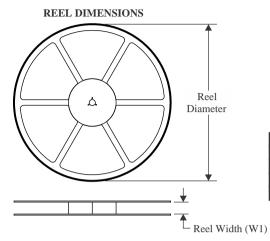
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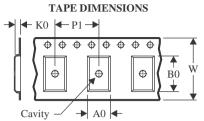
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

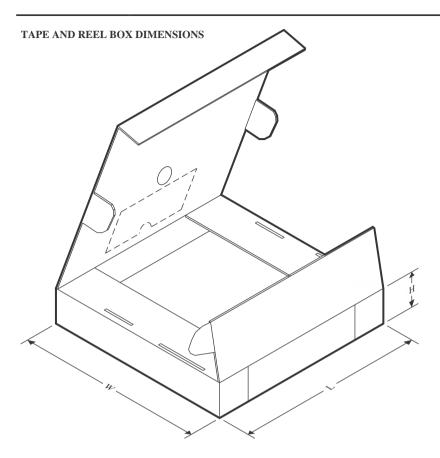
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD95372BQ5M	LSON- CLIP	DQP	12	2500	330.0	12.4	5.3	6.3	1.8	8.0	12.0	Q1
CSD95372BQ5MG4	LSON- CLIP	DQP	12	2500	330.0	12.4	5.3	6.3	1.8	8.0	12.0	Q1
CSD95372BQ5MT	LSON- CLIP	DQP	12	250	180.0	12.4	5.3	6.3	1.8	8.0	12.0	Q1

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*All dimensions are nominal

	,						
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD95372BQ5M	LSON-CLIP	DQP	12	2500	346.0	346.0	33.0
CSD95372BQ5MG4	LSON-CLIP	DQP	12	2500	346.0	346.0	33.0
CSD95372BQ5MT	LSON-CLIP	DQP	12	250	210.0	185.0	35.0

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